

Amendments to the Specification

At p. 1, before paragraph [0001], insert the following:

--CROSS REFERENCE TO RELATED APPLICATION

[0001] This application is a continuation of U.S. Application No. 10/134,201 filed on April 25, 2002.

Please amend paragraph 7 as follows:

[0007] A suitable semiconductor substrate can ~~encompasses~~ encompass a semiconductive portion and an overlying insulative portion. For embodiments that encompass a recess, such recess can be formed within the insulative portion. In some embodiments the recess extends to expose, at a bottom and/or sidewalls of the recess, a portion of the semiconductive portion or a portion of a conductive device formed over or in the semiconductive portion. Where the material encompasses a conductive material, electrical communication between the conductive material and the semiconductive portion or conductive device can be provided through the bottom or sidewalls of the recess. In some embodiments of the present invention, the material can include more than one layer. For example, the material can encompass a first layer of a first composition and a second layer of a second composition overlying the first layer. The two compositions can be, for example, a first composition comprising ~~metal and both of nitrogen~~ metal, nitrogen, and silicon (such as TaSiN); and a second composition consisting essentially of metal and nitrogen (such as TaN).

Please amend paragraph 49 as follows:

[0049] Referring to Fig. 10, a structure is illustrated subsequent to the processing of Figs. 9A or 9A, 9B, and specifically, subsequent to the removal of resist plugs 42a or 42b. Plugs 42a or 42b can be removed by employing a chemical solution or plasma tailored to remove the material of the plugs. Where plugs 42a and/or 42b are a photoresist material, one exemplary removal method is an oxygen plasma, although any appropriate method can be used. As seen, material layer 30 is transformed into layer 36 entirely within recess 20 and adjacent bottom 22 and sidewalls 24 of such recess 20. Layer 36 can be, for example, an electrode of a capacitor structure, some or all of which to be formed within recess 20. Advantageously, the structure depicted in Fig. 10 has been formed without a photomasking step subsequent to the forming of recess 20. Rather, as shown above, the patterning to form layer 36 within recess 20 can be accomplished, in some embodiments, using essentially blanket depositions and CMP processing only. In other embodiments, chemical or plasma processing can be used, after the forming of plug 42 (Fig. 8), to define layer 36 as discussed above, also without the need for a photomasking step.